N-Channel Enhancement Mode Power MOSFET

General Description

The series of Power MOSFETs use advanced technology and design.This high voltage MOSFET fits Switched applications.

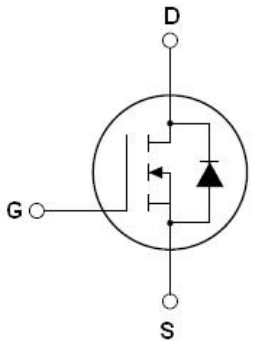
$V_{DS\ min@Tjmax}$	1650	V
$R_{DS(ON)TYP}$	5.5	Ω
ID	3	A
Qg	32	nC

Features

- High speed switching
- Intrinsic capacitances and Qg minimized
- 100% Avalanche Tested

Application

- Switched applications



Schematic diagram

Package Marking And Ordering Information

Device	Device Package	Marking
NCE3N150D	TO-263-2L	NCE3N150D

TO-263-2L

Table 1. Absolute Maximum Ratings (T_J=25℃)

Parameter	Symbol	NCE3N150D	Unit
Drain-Source Voltage (VGS=0V)	V_{DS}	1500	V
Gate-Source Voltage (VDS=0V) DC	V_{GS}	±30	V
Continuous Drain Current at Tc=25°C	$I_{D\ (DC)}$	3	A
Continuous Drain Current at Tc=100°C	$I_{D\ (DC)}$	2.1	A
Pulsed drain current (Note 1)	$I_{DM\ (pluse)}$	9	A
Maximum Power Dissipation(Tc=25°C) Derate above 25°C	P_D	187 1.24	W W/°C
Single pulse avalanche energy (Note 2)	E_{AS}	225	mJ
Single pulse avalanche current (Note 2)	I_{AS}	3	A
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55...+175	°C

* limited by maximum junction temperature

Table 2. Thermal Characteristic

Parameter	Symbol	NCE3N150D	Unit
Thermal Resistance，Junction-to-Case（Maximum）	R_{thJC}	0.8	°C /W
Thermal Resistance，Junction-to-Ambient （Maximum）	R_{thJA}	50	°C /W

Table 3. Electrical Characteristics (T_J=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=1mA	1500			V
Zero Gate Voltage Drain Current(Tc=25℃)	I_{DSS}	V_{DS}=1500V,V_{GS}=0V			1	μA
Zero Gate Voltage Drain Current(Tc=125℃)	I_{DSS}	V_{DS}=1500V,V_{GS}=0V			100	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±30V,V_{DS}=0V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	3	4	5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=1.5A		5.5	7.5	Ω
Dynamic Characteristics						
Input Capacitance	C_{lss}	V_{DS}=40V,V_{GS}=0V, F=1.0MHz		1700		pF
Output Capacitance	C_{oss}			61		pF
Reverse Transfer Capacitance	C_{rss}			5.5		pF
Total Gate Charge	Q_g	V_{DS}=1200V,I_D=1.5A, V_{GS}=10V		32		nC
Gate-Source Charge	Q_{gs}			8.7		nC
Gate-Drain Charge	Q_{gd}			12		nC
Intrinsic gate resistance	R_G	f = 1 MHz open drain		2		Ω
Switching times						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=750V,I_D=1.5A, R_G=3Ω,V_{GS}=10V		22		nS
Turn-on Rise Time	t_r			45		nS
Turn-Off Delay Time	$t_{d(off)}$			42		nS
Turn-Off Fall Time	t_f			58		nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I_{SD}	T_C=25°C			3	A
Pulsed Source-drain current(Body Diode)	I_{SDM}				9	A
Forward On Voltage	V_{SD}	Tj=25°C,I_{SD}=3A,V_{GS}=0V		0.8	1.1	V
Reverse Recovery Time	t_{rr}	Tj=25°C,I_F=3A, di/dt=100A/μs		390		nS
Reverse Recovery Charge	Q_{rr}			2.2		uC
Peak Reverse Recovery Current	I_{rrm}			11		A

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2. Tj=25℃,VDD=50V,VG=10V, R_G=25Ω

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure1. Safe operating area

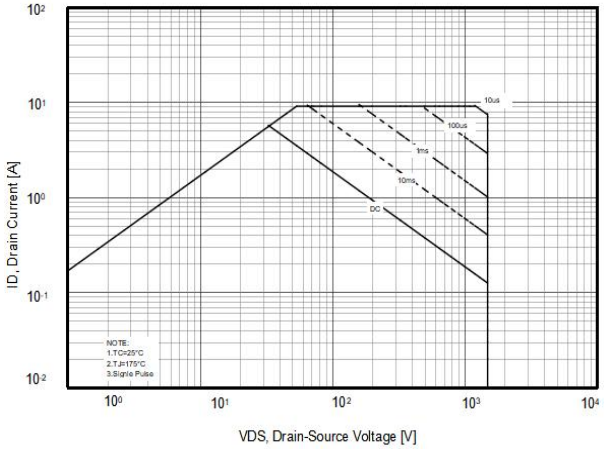


Figure2. Source-Drain Diode Forward Voltage

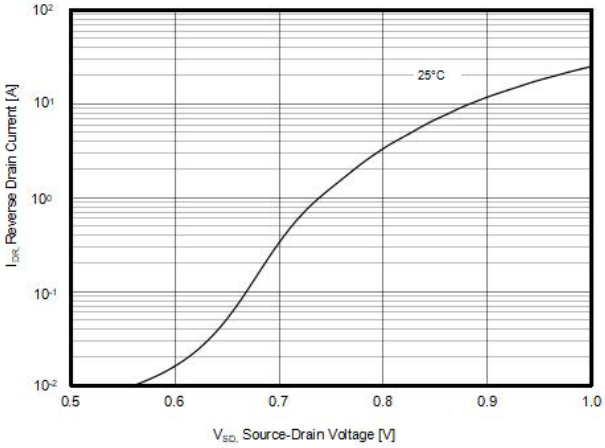


Figure3. $R_{DS(ON)}$ vs Junction Temperature

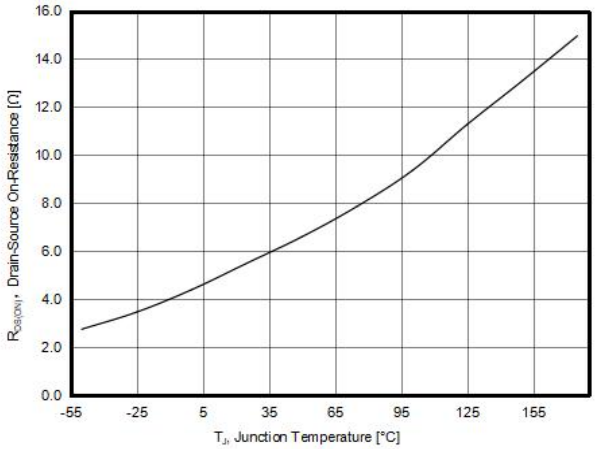


Figure4. BV_{DSS} vs Junction Temperature

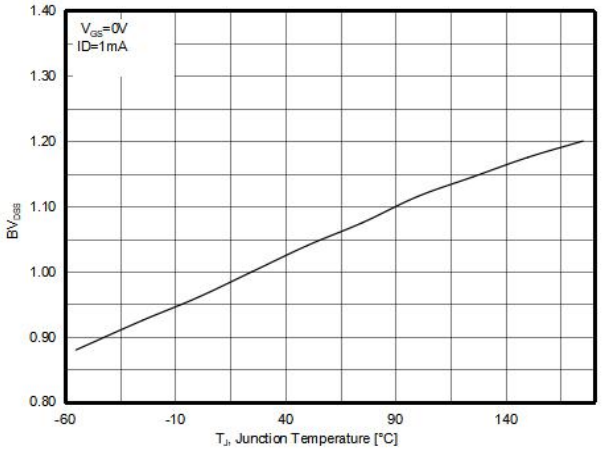


Figure5. Maximum I_D vs Junction Temperature

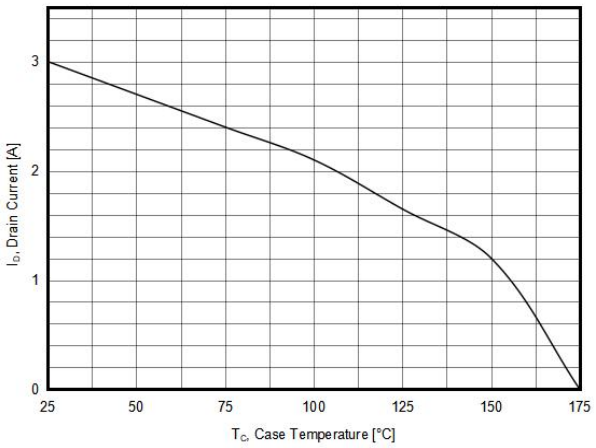


Figure6. Output characteristics

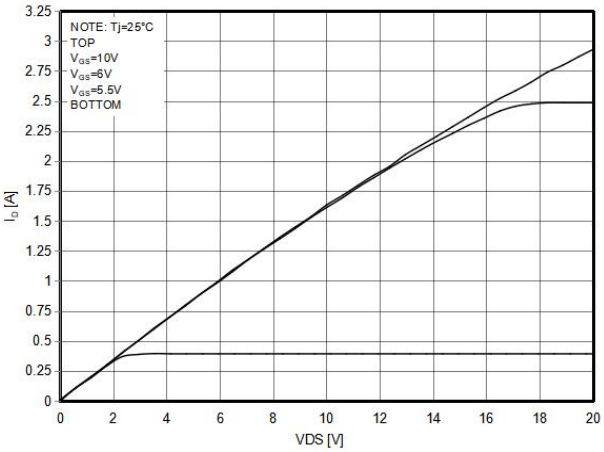


Figure7. Capacitance

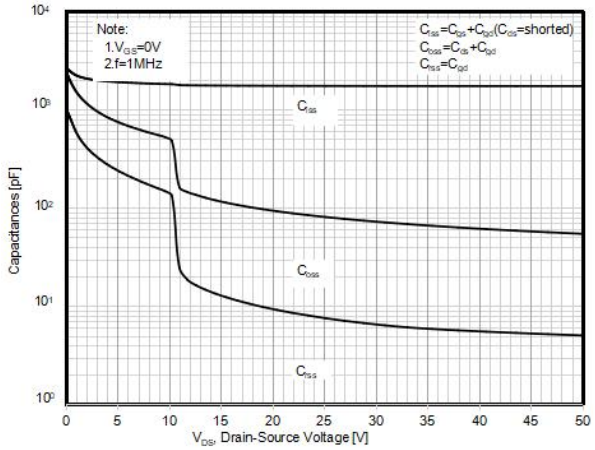


Figure8. Transfer characteristics

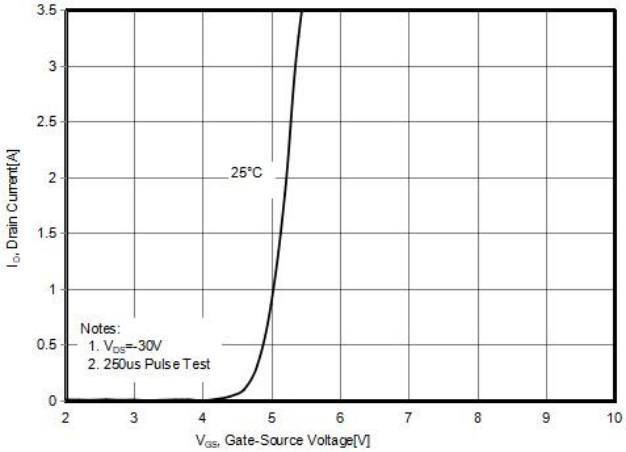


Figure9. Static drain-source on resistance

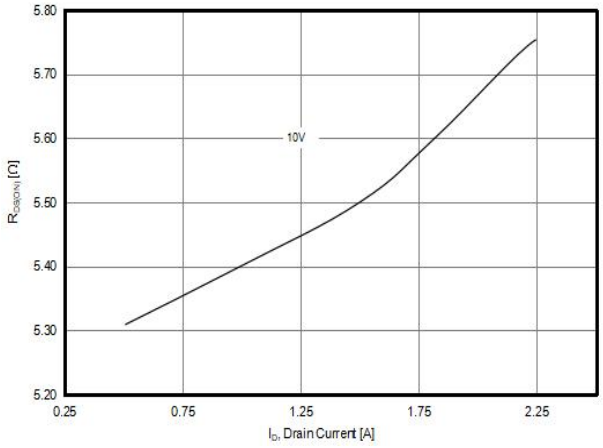
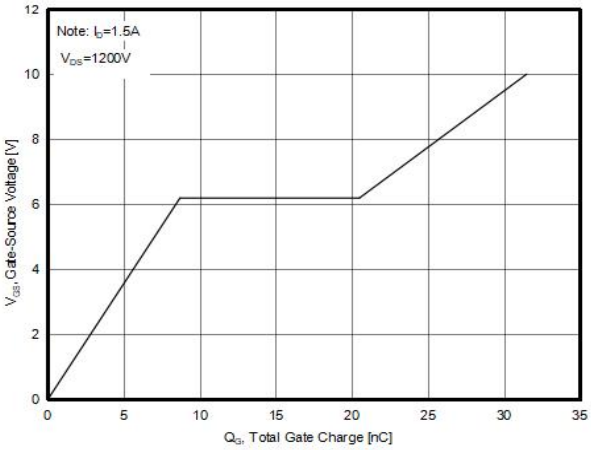
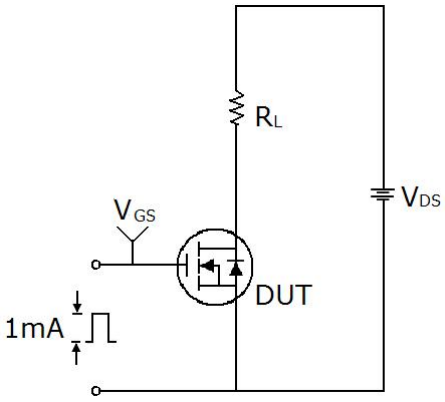


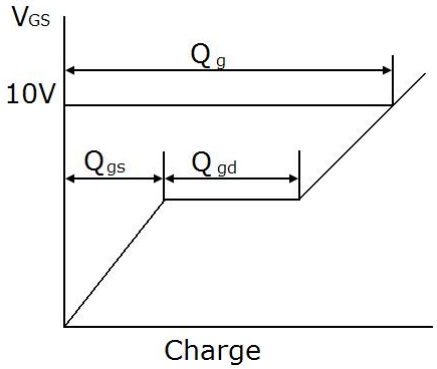
Figure9. Gate charge waveforms



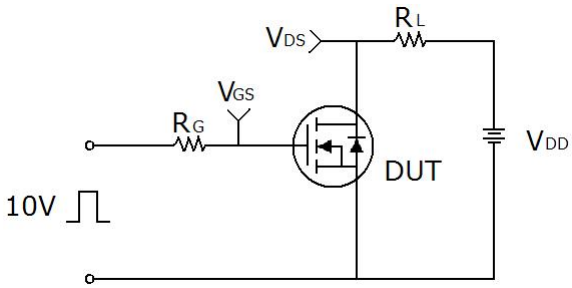
Test circuit

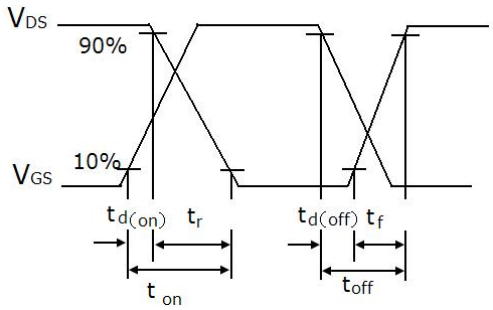
1）Gate charge test circuit & Waveform



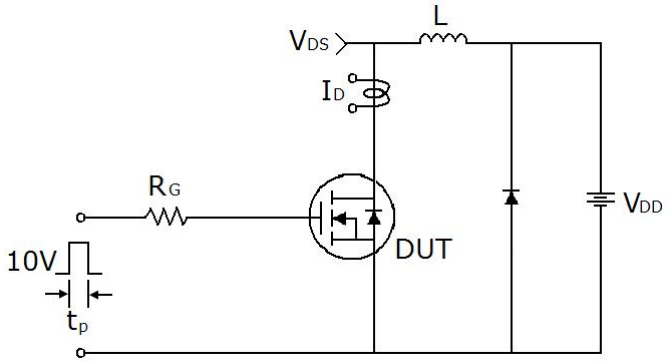


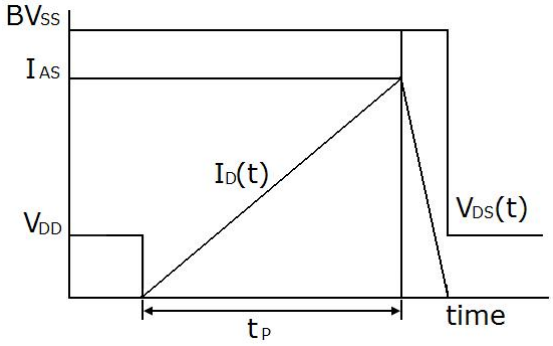
2）Switch Time Test Circuit：



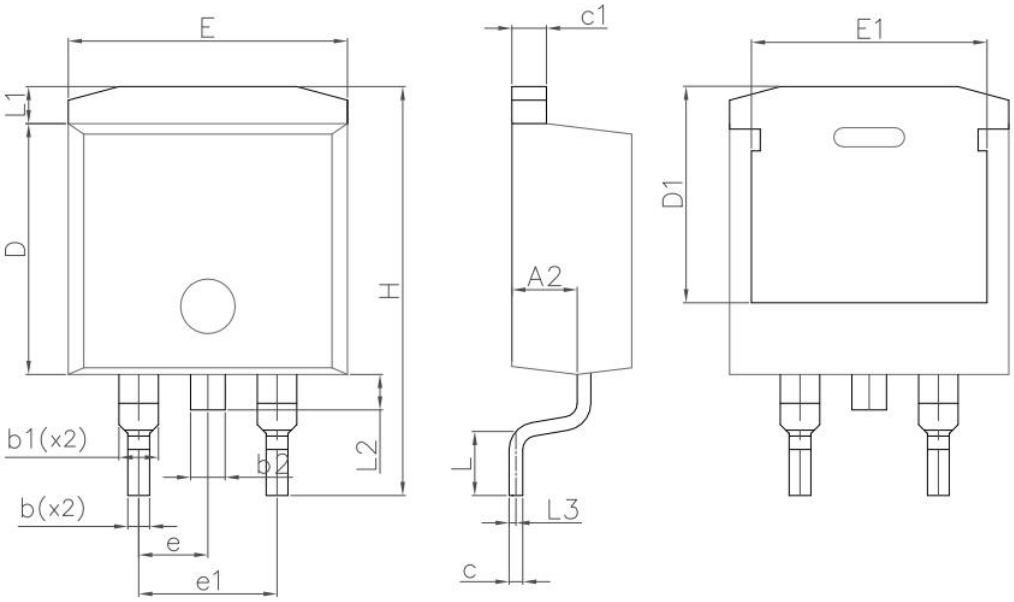


3）Unclamped Inductive Switching Test Circuit & Waveforms



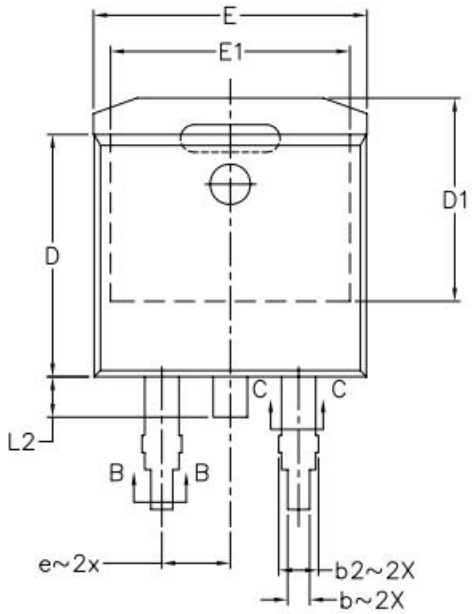


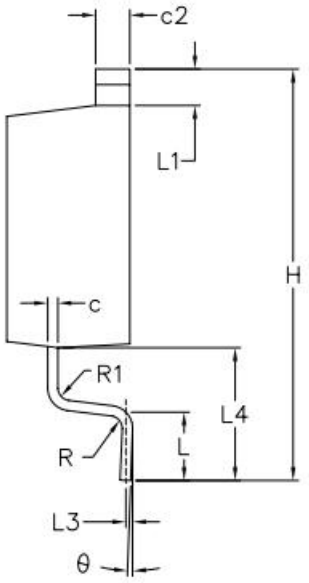
TO-263-2L-E Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A2	4.20	4.60	0.165	0.181
b	0.70	0.90	0.028	0.035
b1	1.20	1.75	0.047	0.069
b2	1.17	1.37	0.046	0.054
c	0.40	0.60	0.016	0.024
c1	1.15	1.40	0.045	0.055
D	9.10	9.30	0.358	0.366
D1	7.63	8.23	0.300	0.324
E	10.05	10.45	0.396	0.411
E1	8.35	8.95	0.329	0.352
e	2.54BSC		0.100BSC	
e1	5.08BSC		0.200BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	1.36REF		0.054REF	
L2	1.30REF		0.051REF	

TO-263-2L-J Package Information





Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380
D1	6.86		0.270	
E	9.65	10.00	0.380	0.394
E1	6.22		0.245	
e	2.54BSC		0.100BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1		1.68		0.066
L2		1.78		0.070
L3	0.25BSC		0.101BSC	
L4	4.78	5.28	0.188	0.208

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